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FDP090N10

N-Channel PowerTrench® MOSFET

100 V, 75 A, 9 mΩ

Features

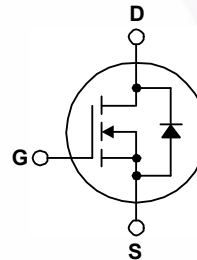
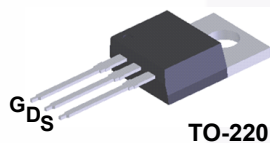
- $R_{DS(on)} = 7.2 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 75 \text{ A}$
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micor Solar Inverter



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDP090N10	Unit
V_{DSS}	Drain to Source Voltage	100	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current	75	A
I_{DM}	Drain Current	300	A
E_{AS}	Single Pulsed Avalanche Energy	309	mJ
I_{AR}	Avalanche Current	75	A
E_{AR}	Repetitive Avalanche Energy	20.8	mJ
dv/dt	Peak Diode Recovery dv/dt	5.6	V/ns
P_D	Power Dissipation	$(T_C = 25^\circ\text{C})$	208
		- Derate Above 25°C	1.39
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FDP090N10	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.72	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP090N10	FDP090N10	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$, $T_C = 25^\circ\text{C}$	100	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	-	0.1	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	-	1	μA
		$V_{DS} = 100 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_C = 150^\circ\text{C}$	-	-	500	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$	2.5	3.5	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 75 \text{ A}$	-	7.2	9	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}$, $I_D = 37.5 \text{ A}$	-	100	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	6185	8225	pF
C_{oss}	Output Capacitance		-	585	775	pF
C_{rss}	Reverse Transfer Capacitance		-	235	355	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50 \text{ V}$, $I_D = 75 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_G = 25 \Omega$	-	107	224	ns	
t_r	Turn-On Rise Time		-	322	655	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4)	-	166	342	ns
t_f	Turn-Off Fall Time		(Note 4)	-	149	309	ns
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 50 \text{ V}$, $I_D = 75 \text{ A}$, $V_{GS} = 10 \text{ V}$	-	89	116	nC	
Q_{gs}	Gate to Source Gate Charge		(Note 4)	-	37	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	22	-	nC

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	75	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	300	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_{SD} = 75 \text{ A}$	-	-	1.25	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}$, $I_{SD} = 75 \text{ A}$,	-	73	-	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt = 100 \text{ A}/\mu\text{s}$	-	166	-	nC

Notes:

- 1: Repetitive rating; pulse-width limited by maximum junction temperature.
- 2: $L = 0.11 \text{ mH}$, $I_{AS} = 75 \text{ A}$, $V_{DD} = 50 \text{ V}$, $R_G = 25 \Omega$, starting $T_J = 25^\circ\text{C}$.
- 3: $I_{SD} \leq 75 \text{ A}$, $di/dt \leq 200 \text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
- 4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

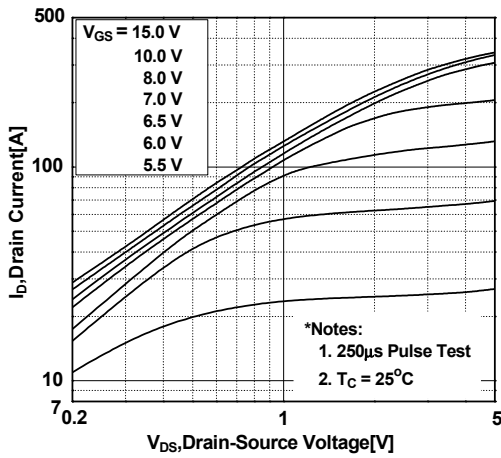


Figure 2. Transfer Characteristics

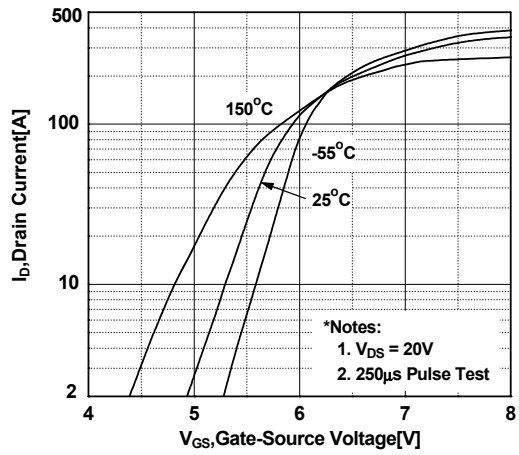


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

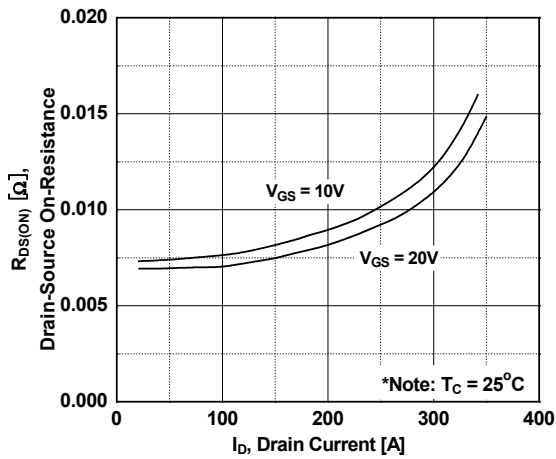


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

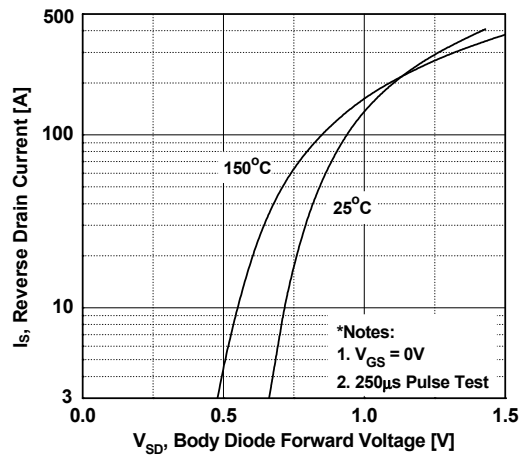


Figure 5. Capacitance Characteristics

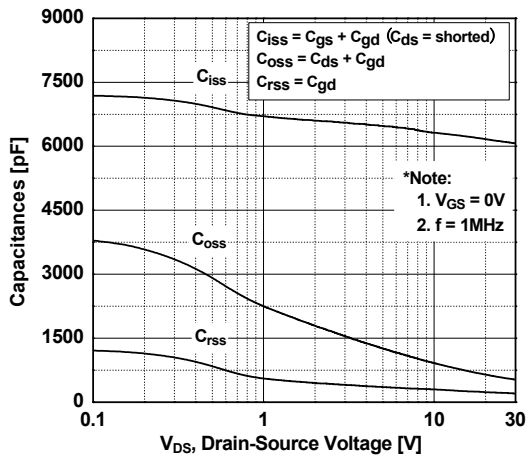
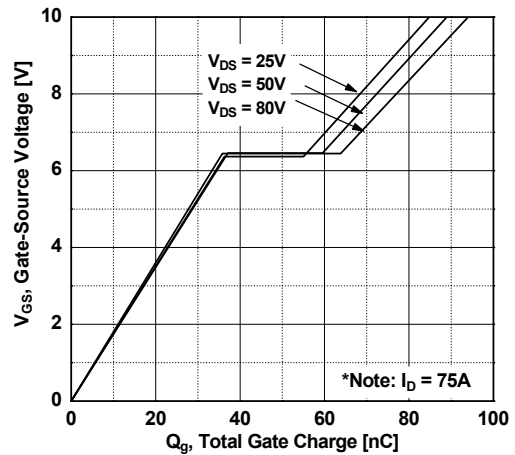


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

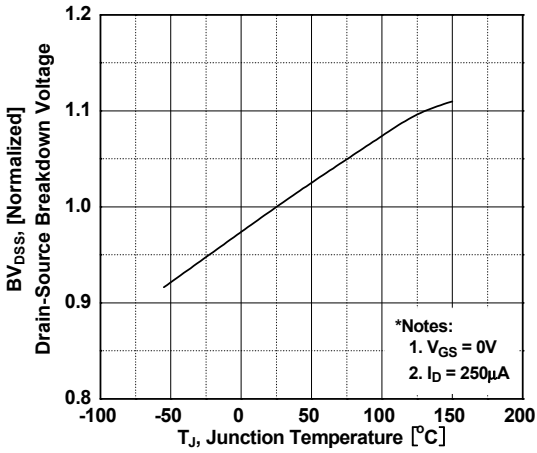


Figure 8. On-Resistance Variation vs. Temperature

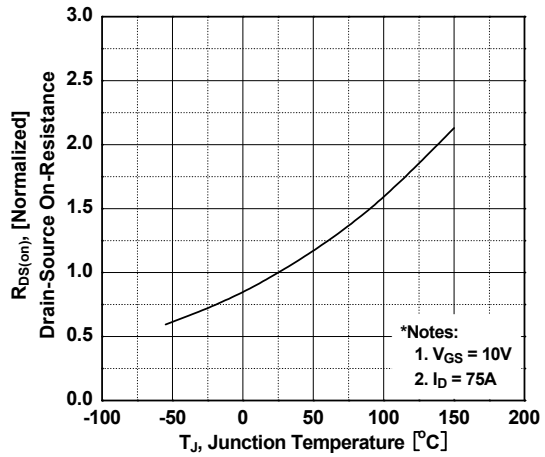


Figure 9. Maximum Safe Operating Area

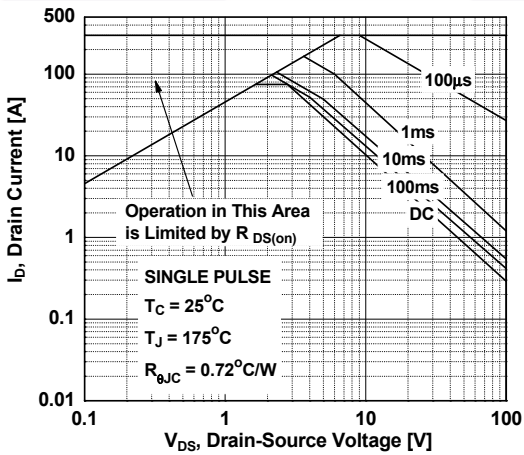


Figure 10. Maximum Drain Current vs. Case Temperature

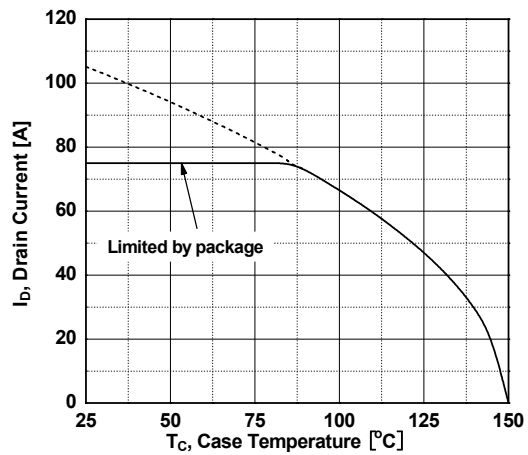


Figure 11. Transient Thermal Response Curve

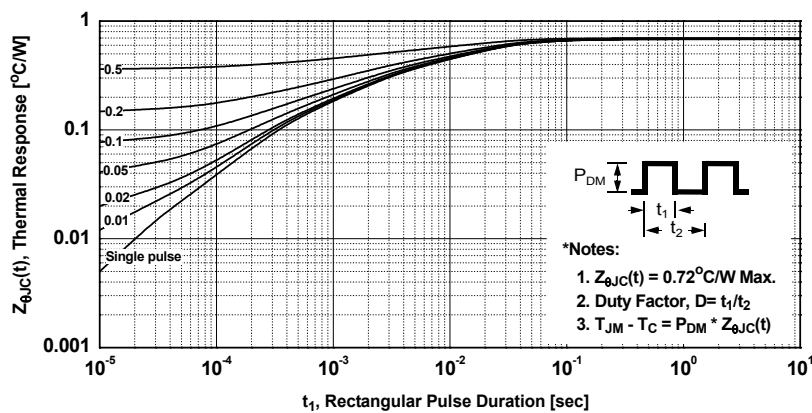




Figure 12. Gate Charge Test Circuit & Waveform



Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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